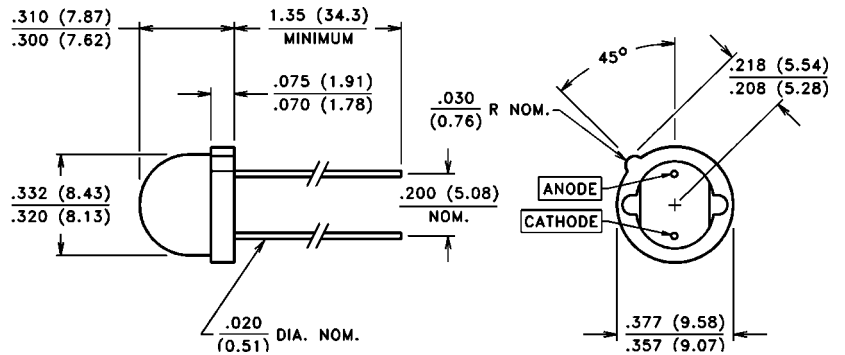


## PACKAGE DIMENSIONS inch (mm)



CASE 12 LENSED CERAMIC  
CHIP ACTIVE AREA: .017 in<sup>2</sup> (1.1 mm<sup>2</sup>)

## PRODUCT DESCRIPTION

Large area planar silicon photodiode mounted on a two lead ceramic substrate. A clear molded lens is used to increase sensitivity. Low junction capacitance permits fast response time.

## ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -20°C to 75°C  
Operating Temperature: -20°C to 75°C

## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, page 46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP1188S			UNITS
			Min.	Typ.	Max.	
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K		200		μA
TC I <sub>SC</sub>	I <sub>SC</sub> Temperature Coefficient	2850 K		.20		%/°C
I <sub>SC</sub>	Short Circuit Current	100 μW/cm <sup>2</sup> , 880 nm	13		25	μA
V <sub>OC</sub>	Open Circuit Voltage	H = 100 fc, 2850 K		.33		mV
TC V <sub>OC</sub>	V <sub>OC</sub> Temperature Coefficient	2850 K		-2.0		mV/°C
I <sub>D</sub>	Dark Current	H = 0, VR = 10 mV		3	30	nA
R <sub>SH</sub>	Shunt Resistance	H = 0, V = 10 mV		67		GΩ
TC R <sub>SH</sub>	R <sub>SH</sub> Temperature Coefficient	H = 0, V = 10 mV		-11		%/°C
C <sub>J</sub>	Junction Capacitance	H = 0, V = 0 V		.18	.30	nF
λ <sub>range</sub>	Spectral Application Range		400		1100	nm
λ <sub>p</sub>	Spectral Response - Peak			925		nm
S <sub>R</sub>	Sensitivity	@ Peak		.55		A/W